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Team Nexperia



PNP resistor-equipped transistor; R1 = 4.7 kΩ, R2 = 47 kΩRev. 1 — 29 June 2012Product data s

Product data sheet

#### **Product profile** 1.

### **1.1 General description**

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC143ZMB.

### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

### **1.3 Applications**

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 gualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	



PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)	1	3
3	0	output (collector)	2 Transparent top view DFN1006B-3 (SOT883B)	1 R1 R2 2 sym003

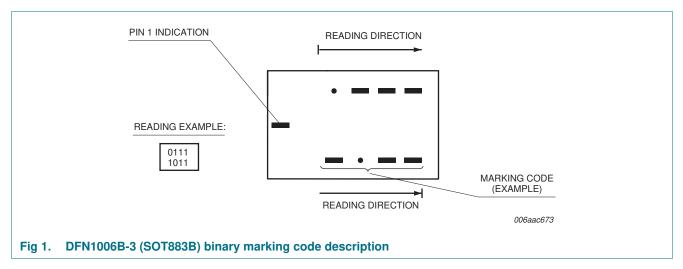
### 3. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PDTA143ZMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B					

### 4. Marking

Table 4.	Marking codes
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Type number	Marking code
PDTA143ZMB	0010 1010



PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

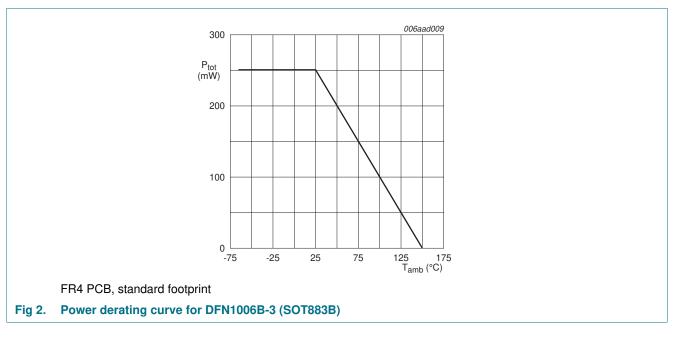
### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
VI	input voltage	positive		-	5	V
		negative		-	-30	V
lo	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



### 6. Thermal characteristics

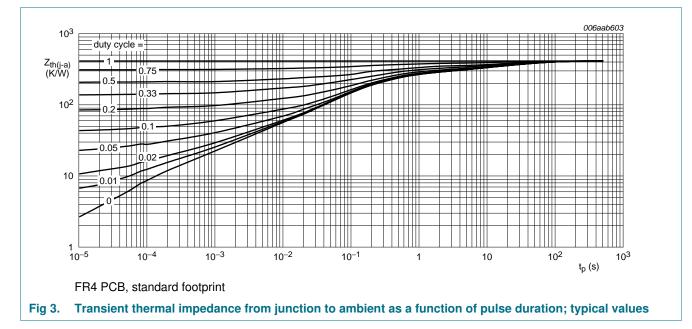
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### **NXP Semiconductors**

# PDTA143ZMB

PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 



### 7. Characteristics

#### Table 7. Characteristics

Parameter	Conditions		Min	Тур	Max	Unit
collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	-100	nA
collector-emitter cut-off	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-1	μA
current	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μA
emitter-base cut-off current	$V_{EB}$ = -5 V; $I_C$ = 0 A; $T_{amb}$ = 25 °C		-	-	-170	μA
DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; $T_{amb}$ = 25 °C		100	-	-	
collector-emitter saturation voltage	$I_{C}$ = -5 mA; $I_{B}$ = -0.25 mA; $T_{amb}$ = 25 °C		-	-	-100	mV
off-state input voltage	$V_{CE} = -5 \ V; \ I_C = -100 \ \mu A; \ T_{amb} = 25 \ ^\circ C$		-	-0.6	-0.5	V
on-state input voltage	$V_{CE} = -0.3 \text{ V}; \text{ I}_{C} = -5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$		-1.3	-0.9	-	V
bias resistor 1 (input)	T <sub>amb</sub> = 25 °C		3.3	4.7	6.1	kΩ
bias resistor ratio			8	10	12	
collector capacitance	$V_{CB}$ = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	-	3	pF
transition frequency	$V_{CE}$ = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	[1]	-	180	-	MHz
	collector-base cut-off currentcollector-emitter cut-off currentemitter-base cut-off currentDC current gain collector-emitter saturation voltageoff-state input voltageon-state input voltagebias resistor 1 (input)bias resistor ratio collector capacitance	$\begin{array}{ll} \mbox{collector-base cut-off} & V_{CB} = -50 \ V; \ I_E = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{current} & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \hline V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{emitter-base cut-off} & V_{EB} = -5 \ V; \ I_C = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{current} & V_{CE} = -5 \ V; \ I_C = -10 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-emitter} & I_C = -5 \ mA; \ I_B = -0.25 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-emitter} & V_{CE} = -5 \ V; \ I_C = -100 \ \muA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-emitter} & V_{CE} = -0.3 \ V; \ I_C = -5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{constate input voltage} & V_{CE} = -0.3 \ V; \ I_C = -5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{bias resistor 1 (input)} & T_{amb} = 25 \ ^{\circ}C \\ \mbox{bias resistor ratio} & V_{CB} = -10 \ V; \ I_E = 0 \ A; \ I_e = 0 \ A; \\ \mbox{f} = 1 \ MHz; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{transition frequency} & V_{CE} = -5 \ V; \ I_C = -10 \ mA; \ f = 100 \ MHz; \end{array}$	$\begin{array}{c} \mbox{collector-base cut-off current} & V_{CB} = -50 \ V; \ I_E = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \ & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \ & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_j = 150 \ ^{\circ}C \ & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_j = 150 \ ^{\circ}C \ & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \ & V_{CE} = -5 \ V; \ I_C = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & I_C = -5 \ V; \ I_C = -10 \ mA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & I_C = -5 \ M; \ I_B = -0.25 \ mA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & I_C = -5 \ V; \ I_C = -100 \ \muA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & V_{CE} = -5 \ V; \ I_C = -5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & V_{CE} = -0.3 \ V; \ I_C = -5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & V_{CE} = -0.3 \ V; \ I_C = -5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & V_{CE} = -0.3 \ V; \ I_C = -5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & V_{CE} = -10 \ V; \ I_E = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & V_{CE} = -10 \ V; \ I_E = 0 \ A; \ & T_{amb} = 25 \ ^{\circ}C \ & Collector-emitter \ & Collector-emitter$	$\begin{array}{c c} \mbox{collector-base cut-off} & V_{CB} = -50 \ V; \ I_E = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C & - \\ \hline & \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ - -   collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ - -   witter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ - -   emitter-base cut-off current $V_{CE} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ - -   DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 100 -   collector-emitter saturation voltage $I_C = -5 \text{ mA}; \text{ I}_B = -0.25 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ - -   off-state input voltage $V_{CE} = -5 \text{ V}; \text{ I}_C = -100 \mu\text{ A}; T_{amb} = 25 \text{ °C}$ - -   off-state input voltage $V_{CE} = -5 \text{ V}; \text{ I}_C = -5 \text{ mA}; T_{amb} = 25 \text{ °C}$ - -   bias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ - - -   bias resistor ratio $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; i_e = 0 \text{ A};$ - - -   collector capacitance $V_{CB} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; f = 100 \text{ MHz};$ - - - -   transition frequency $V_{CE} = -5 \text{ V}; \text{ I}_C =$	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

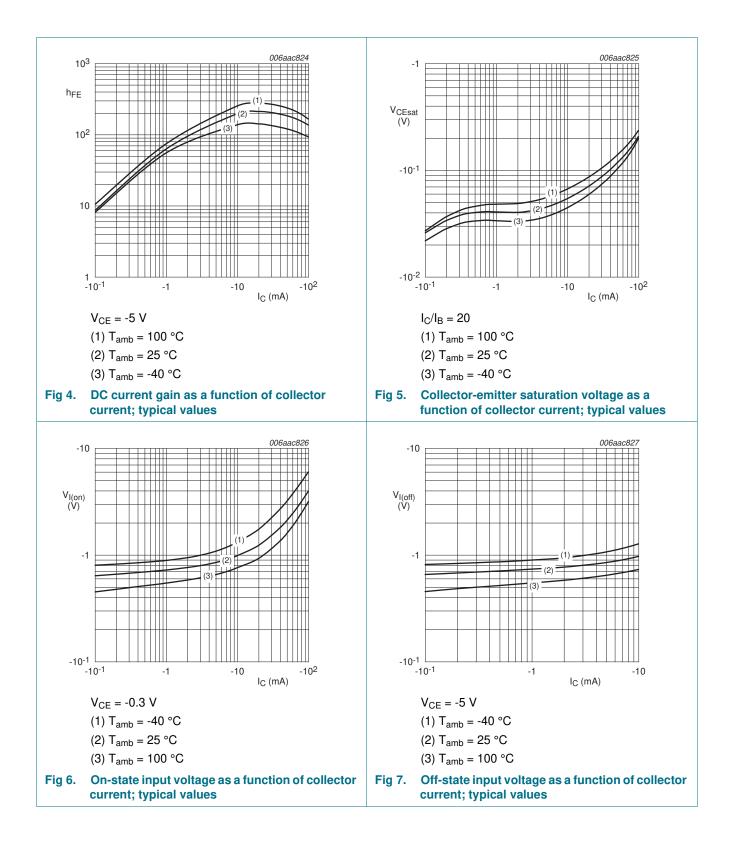
[1] Characteristics of built-in transistor.

PDTA143ZMB Product data sheet

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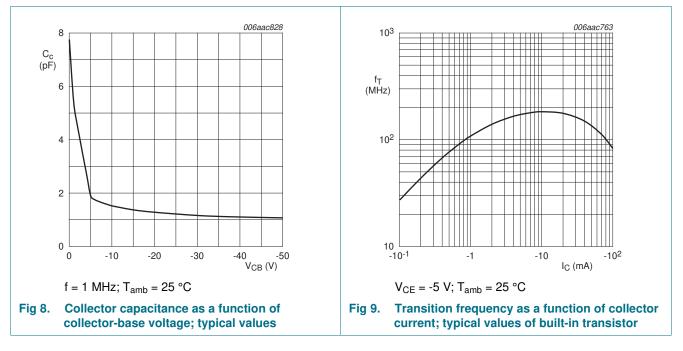
# PDTA143ZMB

#### PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$



### **NXP Semiconductors**

PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 



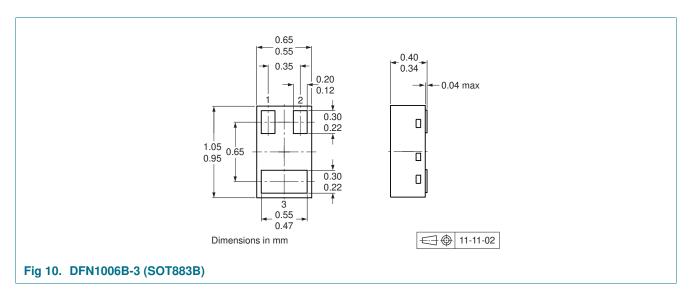
### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

#### Package outline 9.



### 10. Soldering

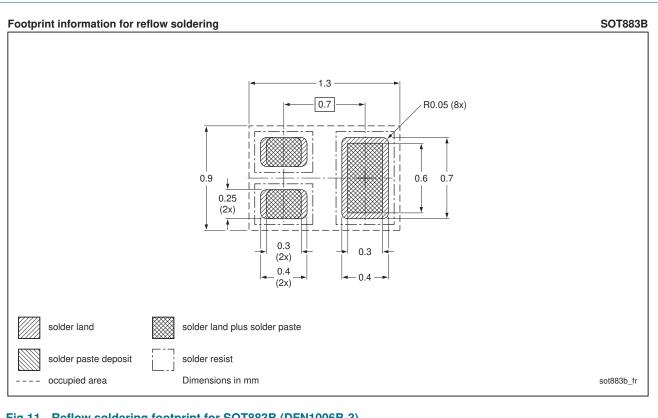


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

PDTA143ZMB **Product data sheet** 

PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

# **11. Revision history**

Table 8. Revision	3. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PDTA143ZMB v.1	20120629	Product data sheet	-	-				

### 12. Legal information

### 12.1 Data sheet status

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

PDTA143ZMB

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#### PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

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